

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)
3025.1US (95-1003.1)

Application Number
09/506,204
Applicant **Trung T. Doan**Filing Date **February 17, 2000**Group Art Unit **Unknown**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TN	5,527,561	06/1996	Dobson			
TN	5,985,763	11/1999	Hong et al.	438	688	
TN	5,998,296	12/1999	Saran et al.	438	685	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Quach

DATE CONSIDERED

11/3/00

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) 3025.1US (95-1003.1)		Application Number Not Yet Assigned 09/506,204	
				Applicant Trung T. Doan		Filing Date February 17, 2000	
				Group Art Unit Unknown 2811			

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TH	5,355,020	10/11/94	Lee et al.	257	741	
TH	5,512,512	04/30/96	Isobe			

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
TH		Dixit et al., "A Novel High Pressure Low Temperature Aluminum Plug Technology For Sub-0.5 μ m Contact/Via Geometries", <u>IEDM</u> , pp. 105-106, 1994 Dec. 1994, pp. 105-108
TH		Dixit et al., "A Novel 0.25 μ m Via Plug Process Using Low Temperature CVD Al/TiN", <u>IEDM</u> 95 , pp. 1001-1003 Dec. 1995, pp. 1001-1003
TH		Dixit et al., "A reactively sputtered coherent TiN process for sub-0.5 μ m technology", <u>SPIE</u> , Vol. 2090 Multilevel Interconnection; pp. 12-21, 1993.
TH		Dixit et al., "An Integrated Low Resistance Aluminum Plug and Low-k Polymer Dielectric For High Performance 0.25 μ m Interconnects", <u>1996 Symposium on VLSI Technology Digest of Technical Papers</u> , pp. 86-87, 1996.
TH		Dixit et al., "Application of High Pressure Extruded Aluminum to ULSI Metallization", <u>Semiconductor International</u> , pp. 79-85, August 1995.
TH		Jain et al., "Chemical mechanical planarization of multilayer dielectric stacks", <u>SPIE</u> , Vol. 2335, pp. 2-11, 1993 .
TH		Mizobuchi et al., "Application of Force Fill Al-Plug Technology to 64Mb DRAM and 0.35 μ m Logic", <u>1995 Symposium on VLSI Technology Digest of Technical Papers</u> , 45-46.
TH		Ting et al., "Effect of Via Etch Profile and Barrier Metal on Electromigration Performance of W-filled Via Structure in TiN/AlCu/TiN Metallization", <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 391, pp. 453-458, 1995.

EXAMINER <div style="text-align: center; font-size: 1.5em;">Hnuch</div>	DATE CONSIDERED <div style="text-align: center; font-size: 1.5em;">11/03/2000</div>
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